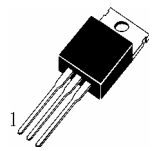
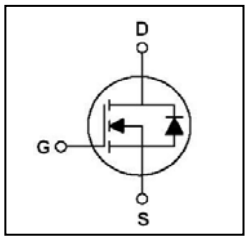
HFP730

N-Channel Enhancement Mode Field Effect Transistor

TO-220



1- G 2-D 3-S



General Description

these power MOSFETs is designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers. And DC-DC&DC-AC Converters for Telecom,Industrial and Consumer Environment

Features

- **5.5A, 400V, R_{DS}(on) <1.0Ω@V_{GS} = 10 V**
- **Fast switching**
- **100% avalanche tested**
- **Improved dv/dt capability**
- **Equivalent Type:IRF730**

Maximum Ratings (Ta=25℃ unless otherwise specified)

T_{stg}——Storage Temperature ---------- -55~150℃

T_j ——Operating Junction Temperature ---------- 150℃

V_{DSS} —— Drain-Source Voltage ----------400V

V_{DGR} —— Drain-Gate Voltage (R_{GS}=20kΩ) ---------- 400V

V_{GSS} —— Gate-Source Voltage ---------- ±20V

I_D —— Drain Current (Continuous) ---------- 5.5A

P_D —— Maximum Power Dissipation ---------- 73W

I_{AR} —— Avalanche Current, Repetitive or Not-Repetitive
(pulse width limited by Tj max, d < 1%) ---------- 5.5 A

E_{AS}—— Single Pulse Avalanche Energy
(starting Tj = 25℃, I_D = I_{AR}, V_{DD} = 50 V) ---------- 330 mJ

E_{AR}—— Repetitive Avalanche Energy(pulse width limited by Tj max, d < 1%) ---------- 7.3mJ

Thermal Characteristics

Symbol	Items	TO-220	Unit
Rthj-case	Thermal Resistance Junction-case	Max 1.71	℃/W
Rthj-amb	Thermal Resistance Junction-ambient	Max 62.5	℃/W
Rth c-s	Thermal Resistance Case-sink	Typ 0.5	℃/W

Electrical Characteristics (Ta=25℃ unless otherwise specified)

Symbol	Items	Min.	Typ.	Max.	Unit	Conditions
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	400			V	I_D=250μA ,V_{GS}=0V
I_{DSS}	Zero Gate Voltage Drain Current			25	μA	V_{DS} =400V, V_{GS}=0V
				250	μA	V_{DS} =320V, V_{GS}=0V,Tj=125℃
I_{GSS}	Gate – Body Leakage			±100	nA	V_{GS}= ±20V , V_{DS} =0V
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	V	V_{DS} = V_{GS} , I_D=250μA
$R_{DS(on)}$	Static Drain-Source On-Resistance			1.0	Ω	V_{GS}=10V, I_D=3A
g_{FS}	Forward Transconductance	2.9			S	V_{DS}=40V, I_D=3A (Note 1)
Dynamic Characteristics and Switching Characteristics						
Ciss	Input Capacitance			1000	pF	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz
Coss	Output Capacitance			100	pF	
Crss	Reverse Transfer Capacitance			26	pF	
$t_{d(on)}$	Turn - On Delay Time			40	nS	V_{DD} = 200 V, I_D = 5.5Apk R_G= 25 Ω (Note 1,2)
tr	Rise Time			120	nS	
$t_{d(off)}$	Turn - Off Delay Time			180	nS	
t_f	Fall Time			110	nS	
Qg	Total Gate Charge			33	nC	V_{DS}=0.8V_{DSS}, ID=5.5A, V_{GS} = 10 V (Note 1,2)
Qgs	Gate–Source Charge		4.3		nC	
Qgd	Gate–Drain Charge		11		nC	
Drain-Source Diode Characteristics and Maximun Ratings						
I_S	Continuous Source–Drain Diode Forward Current			5.5	A	
I_{SM}	Pulsed Drain-Source Diode Forward Current			22	A	
V_{SD}	Source–Drain Diode Forward On–Voltage			1.5	V	I_S=5.5A,V_{GS}=0

Notes:

1. Pulse Test: Pulse width≤300μS, Duty cycle≤2%
2. Essentially independent of operating temperature

Typical Characteristics

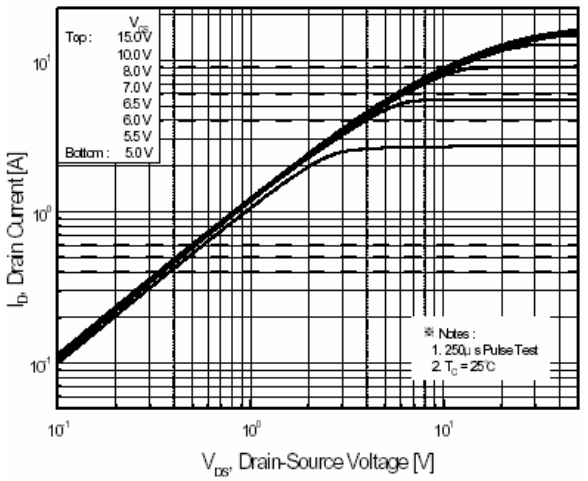


Figure 1. On-Region Characteristics

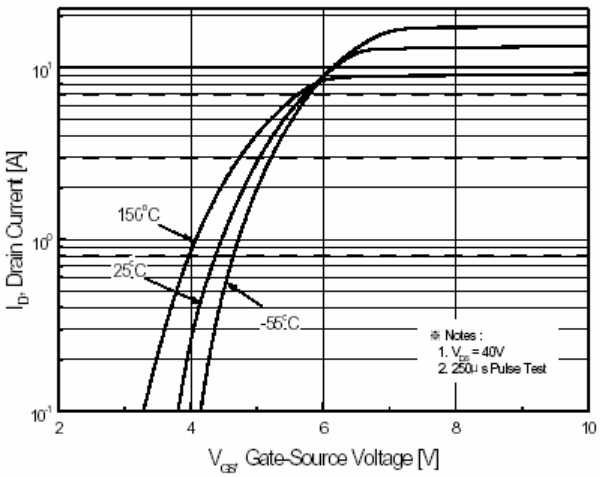


Figure 2. Transfer Characteristics

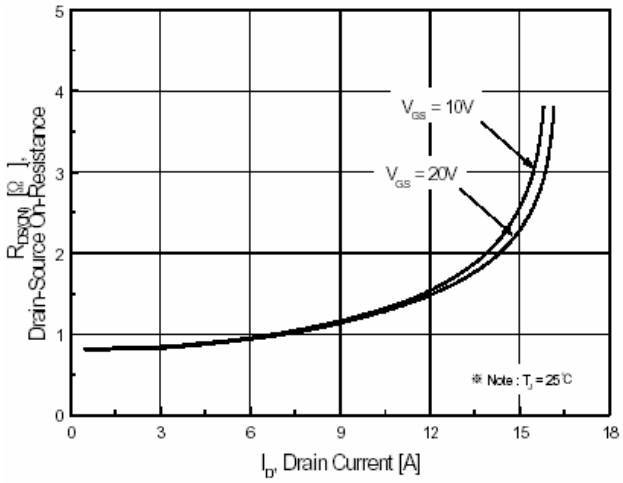


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

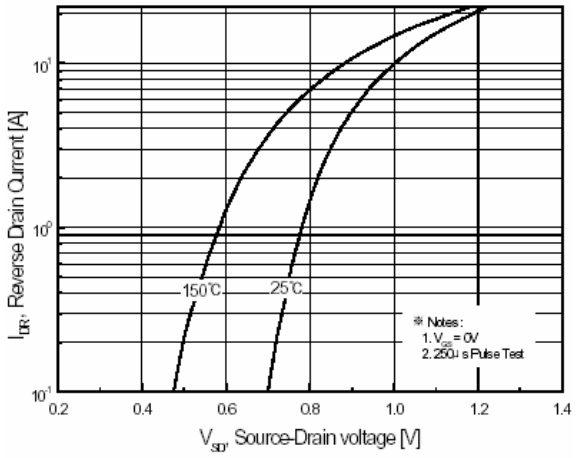


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

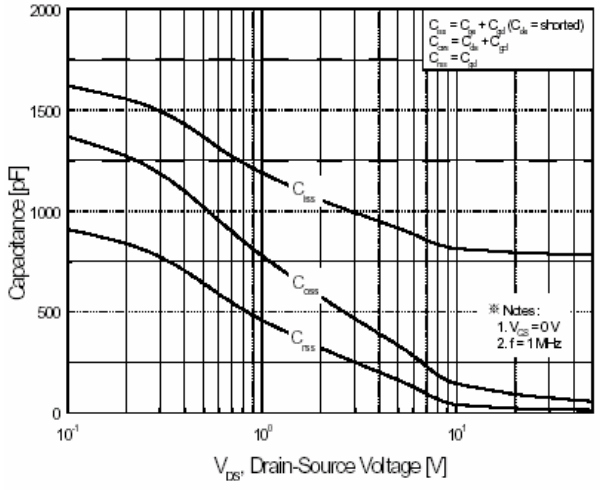


Figure 5. Capacitance Characteristics

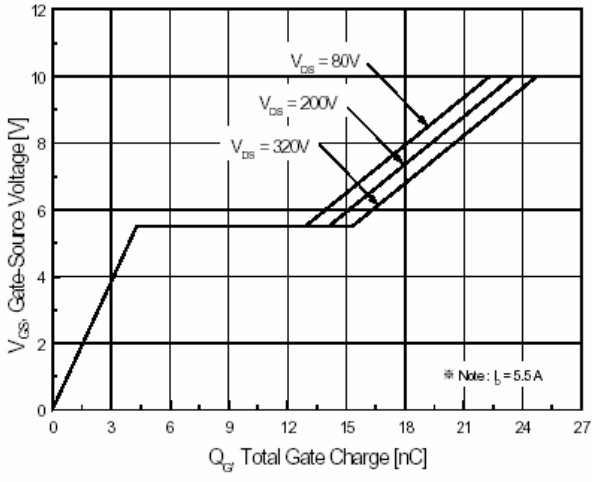


Figure 6. Gate Charge Characteristics

Typical Characteristics

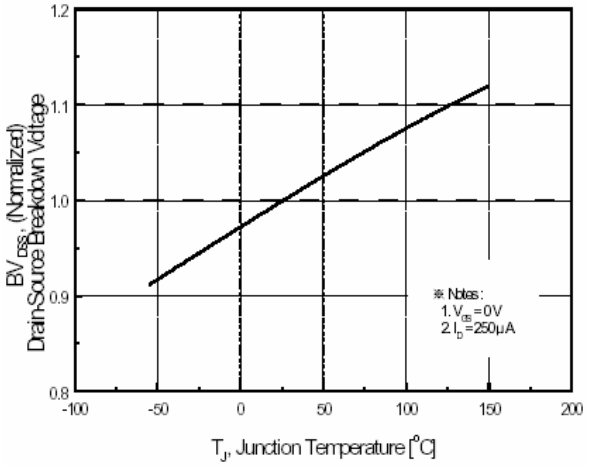


Figure 7. Breakdown Voltage Variation vs Temperature

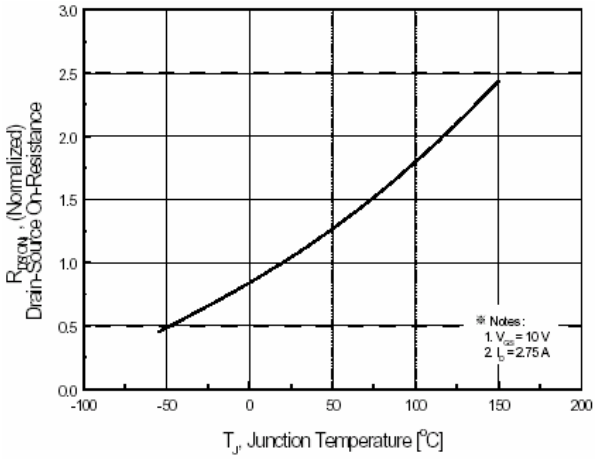


Figure 8. On-Resistance Variation vs Temperature

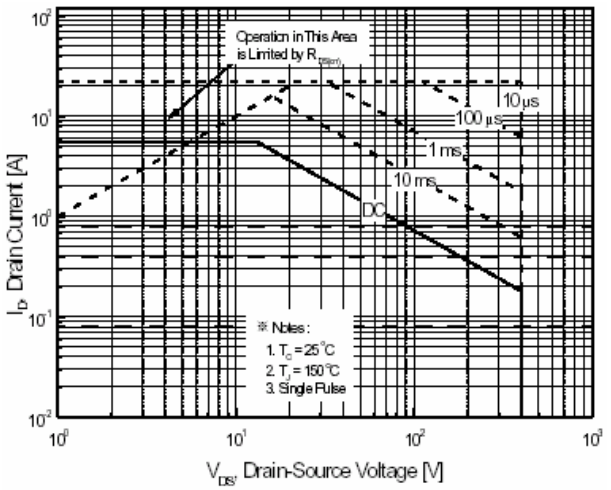


Figure 9. Maximum Safe Operating Area

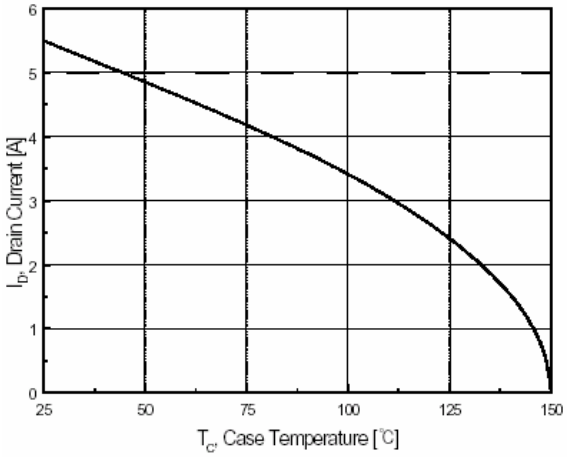


Figure 10. Maximum Drain Current vs Case Temperature

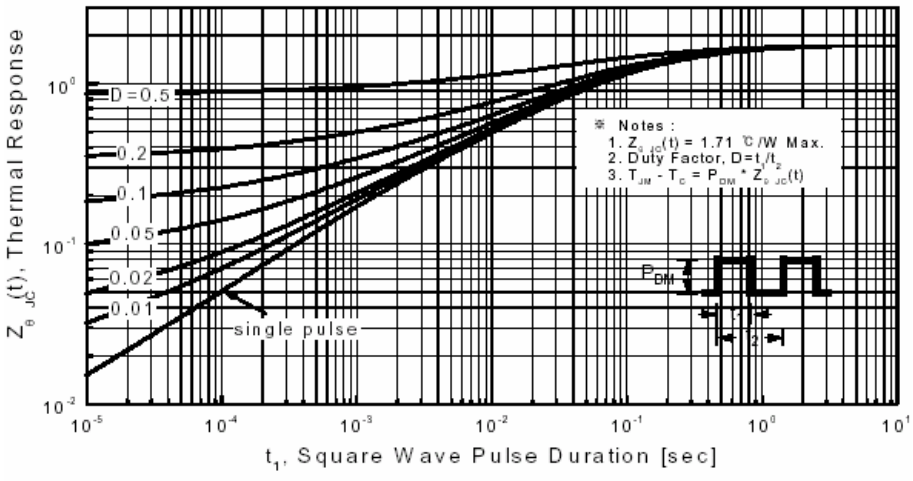
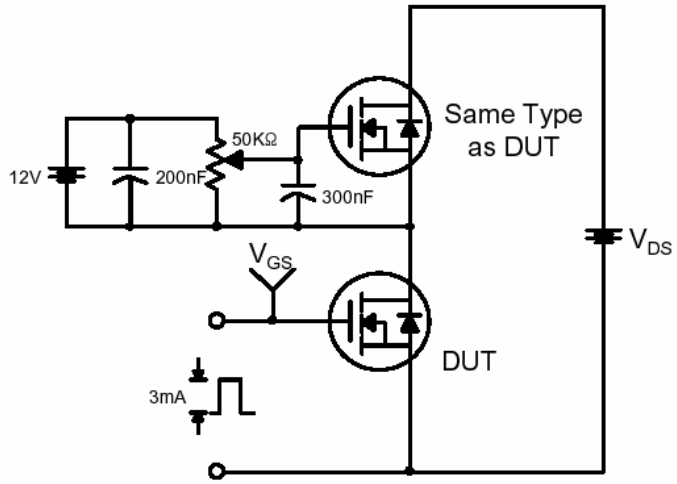
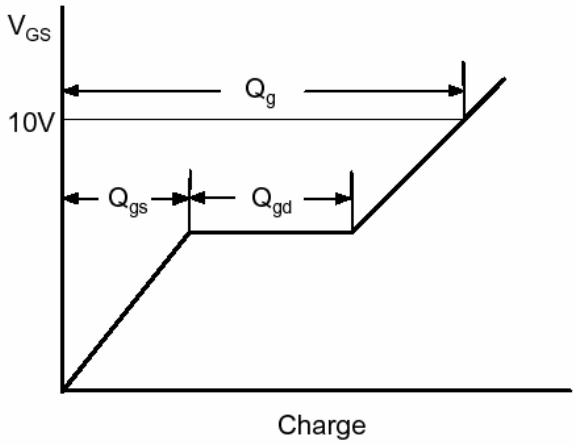


Figure 11. Transient Thermal Response Curve

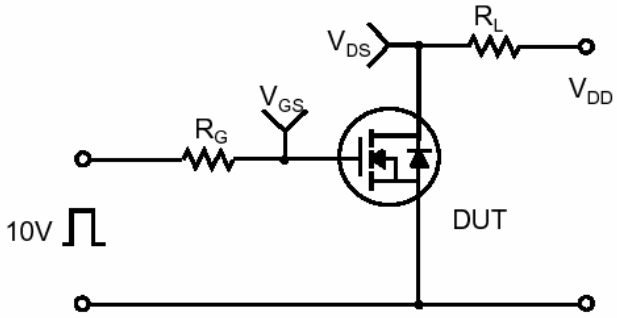
Typical Characteristics

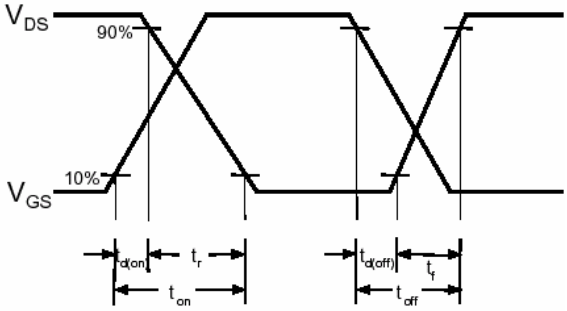
Gate Charge Test Circuit & Waveform



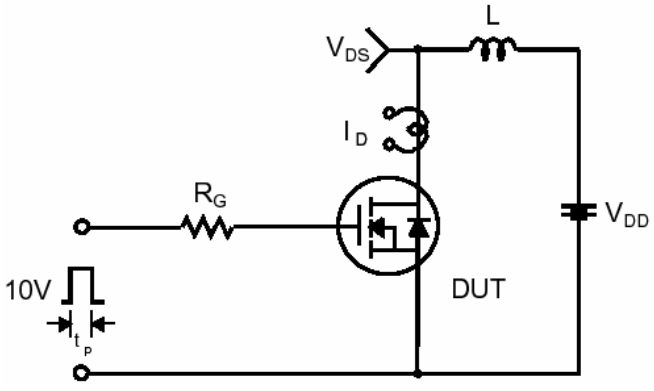


Resistive Switching Test Circuit & Waveforms

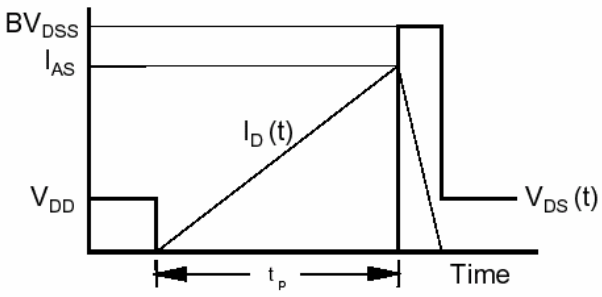




Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Typical Characteristics

Peak Diode Recovery dv/dt Test Circuit & Waveforms

